

CORNERSTONE STANDARD COMPONENTS LIBRARY

(On SOI Platforms)



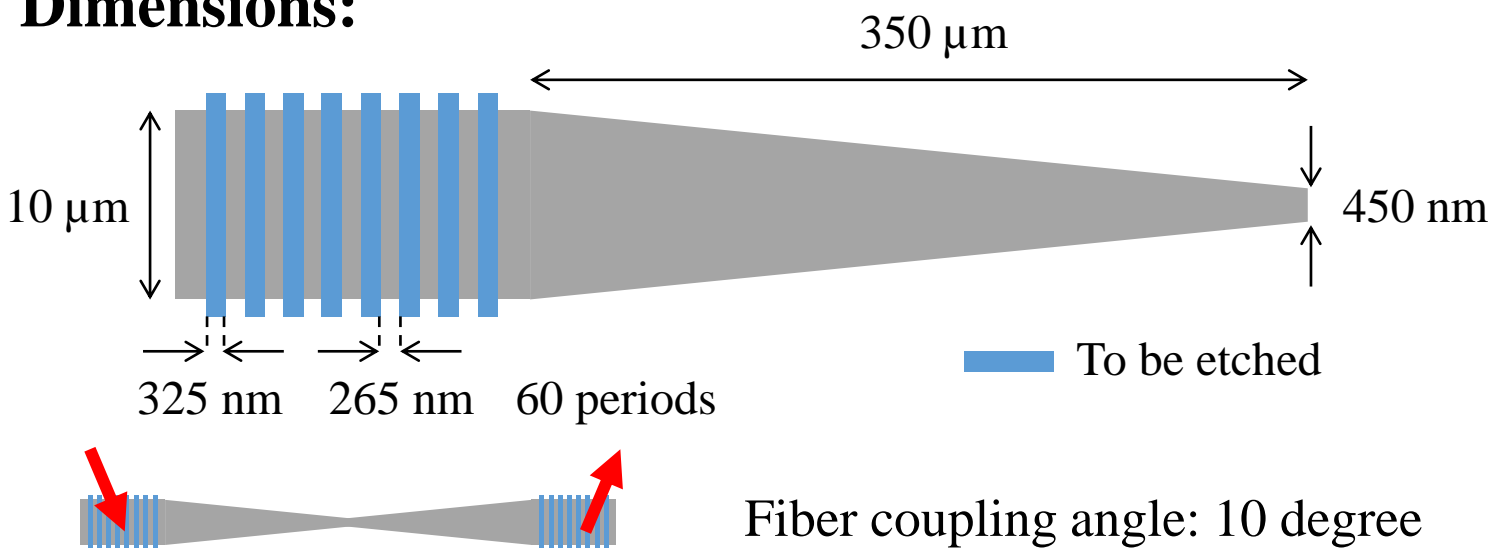


- **Wavelength: 1550 nm**
- **Platform: 340 nm SOI**

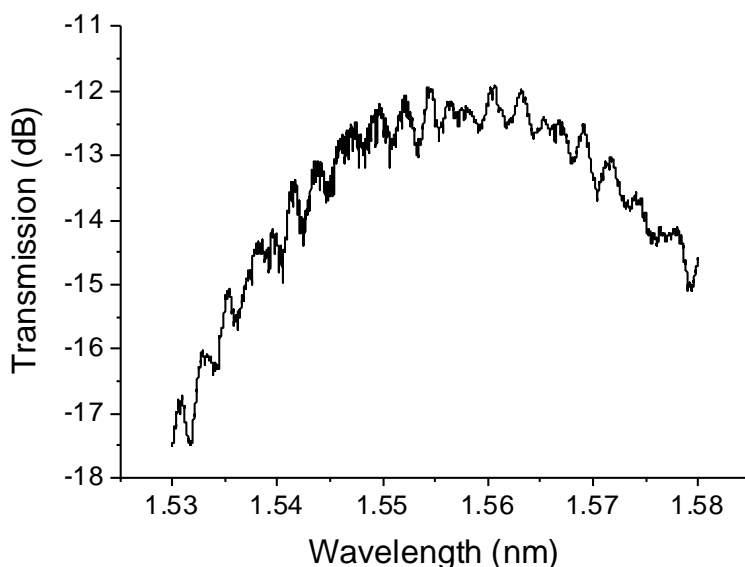
SOI340nm_1550nm_TE_STRIP_Grating_Coupler

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	140 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_STRIP_Grating_Coupler

Dimensions:



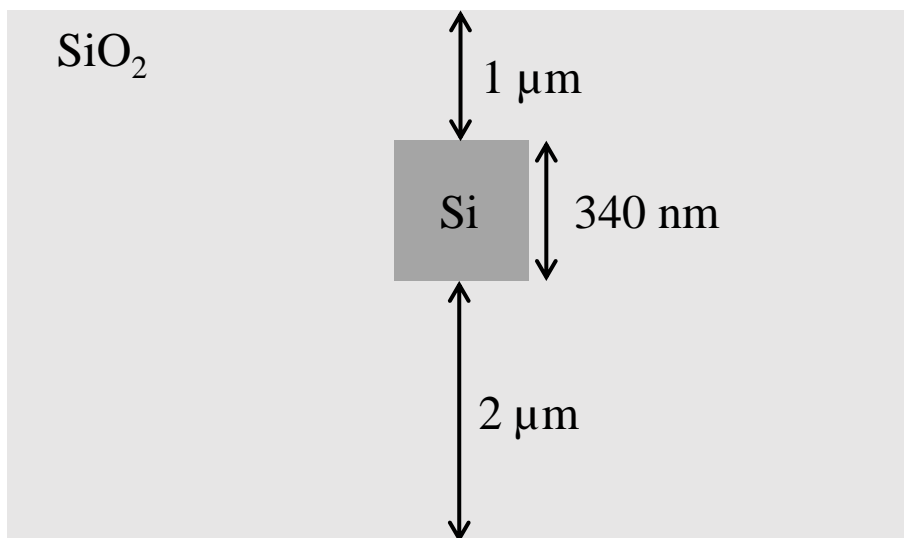
Measured transmission spectrum



Summarized performance:

- Coupling efficiency: 5-7 dB
- 1 dB bandwidth: > 35 nm
- Center wavelength: 1550-1570 nm

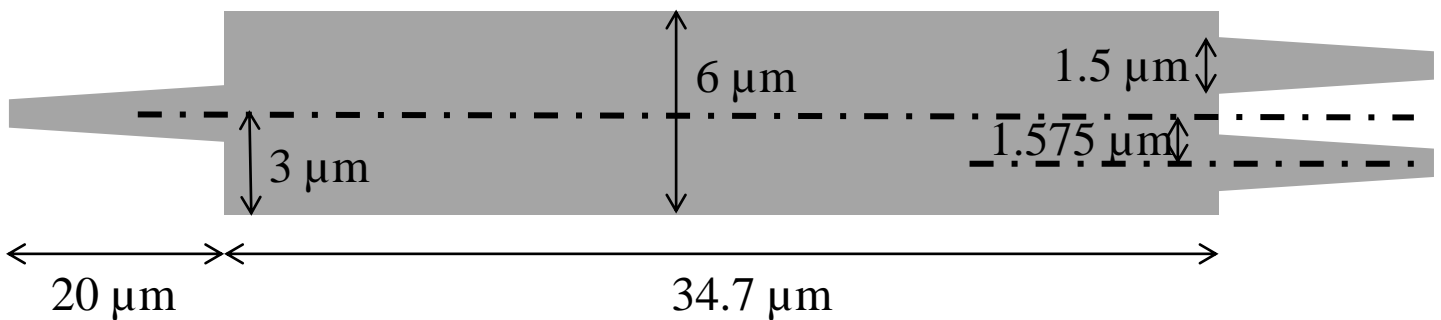
- Wavelength: 1550 nm
- Platform: 340 nm SOI
- **STRIP**



SOI340nm_1550nm_TE_STRIP_2x1_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_STRIP_2x1_MMI

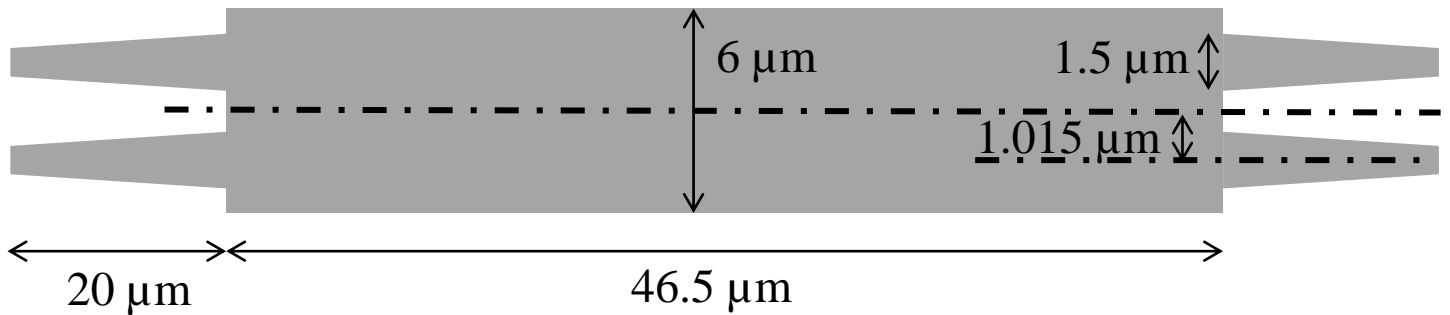
Dimensions:



SOI340nm_1550nm_TE_STRIP_2x2_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1550 nm
Etching depth:	240 nm (Rib design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1550nm_TE_STRIP_2x2_MMI

Dimensions:



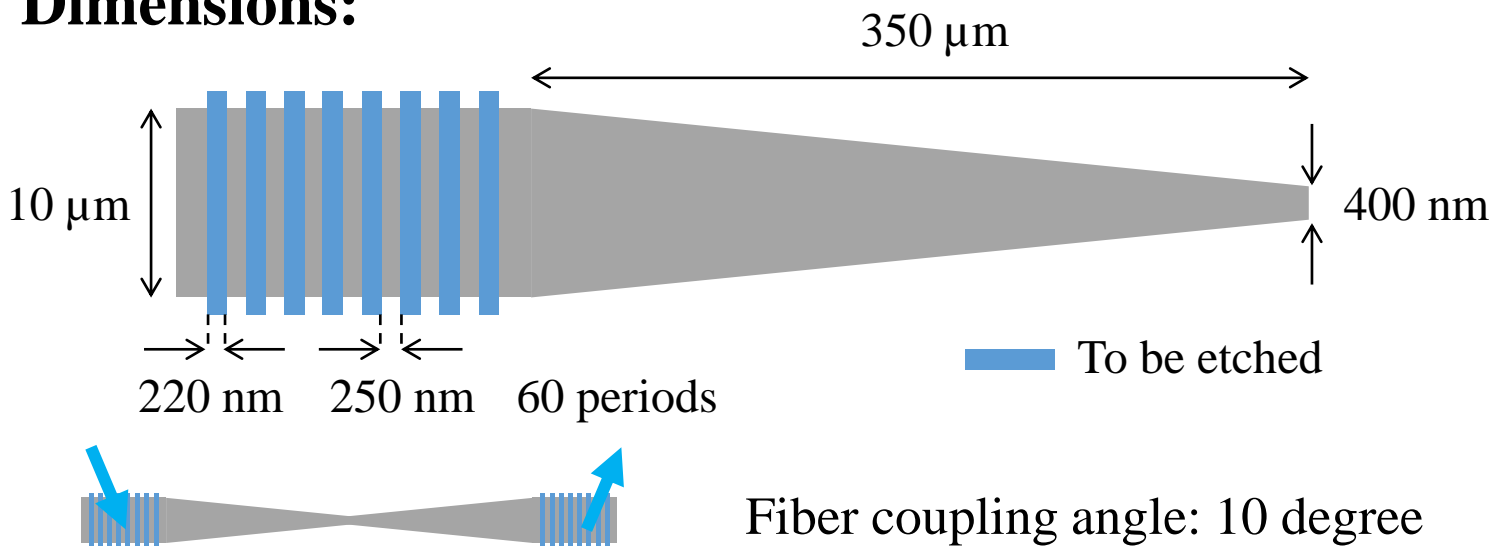


- **Wavelength: 1310 nm**
- **Platform: 340 nm SOI**

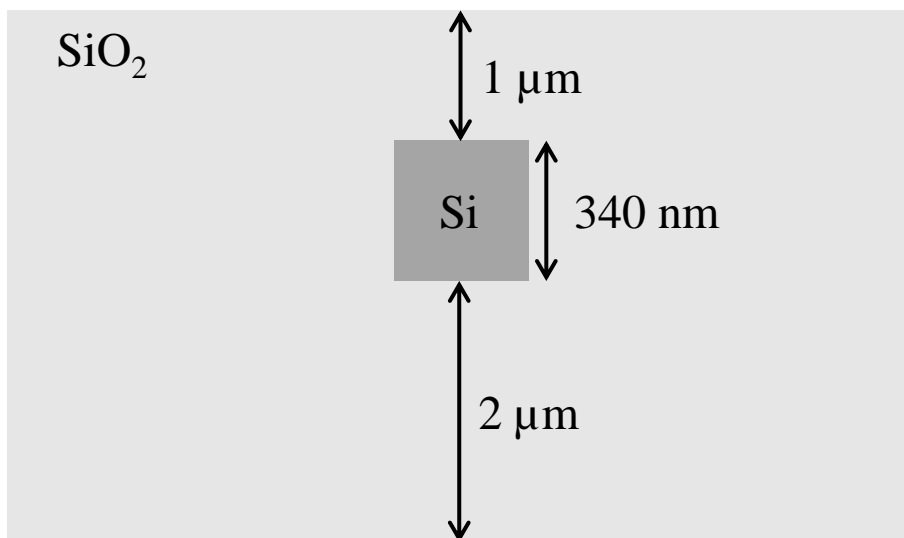
SOI340nm_1310nm_TE_STRIP_Grating_Coupler

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	140 nm (Grating etch depth)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_STRIP_Grating_Coupler

Dimensions:



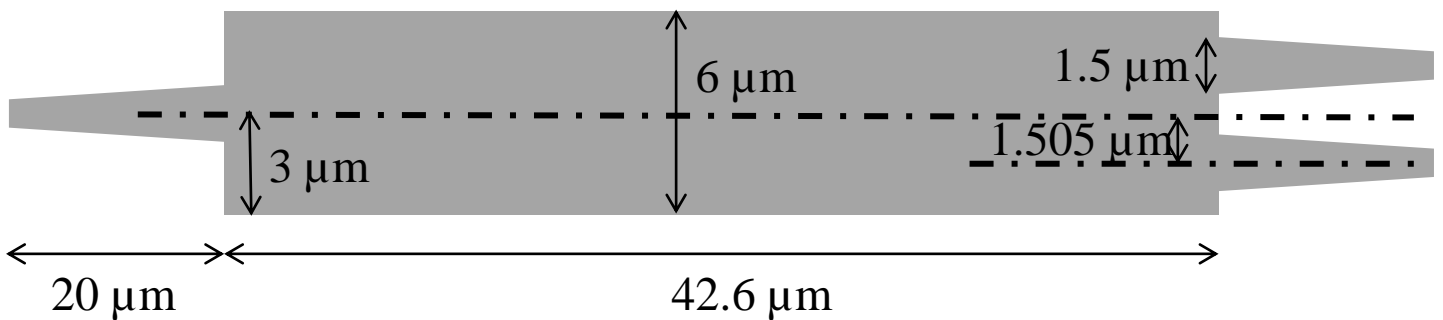
- Wavelength: 1310 nm
- Platform: 340 nm SOI
- **STRIP**



SOI340nm_1310nm_TE_STRIP_2x1_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	340 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_STRIP_2x1_MMI

Dimensions:



SOI340nm_1310nm_TE_STRIP_2x2_MMI

Platform:	340 nm SOI (2 um BOX layer)
Wavelength:	1310 nm
Etching depth:	340 nm (Strip design)
Polarization:	TE
Cell name in GDS lib:	SOI340nm_1310nm_TE_STRIP_2x2_MMI

Dimensions:

